

# DF005S THRU DF10S

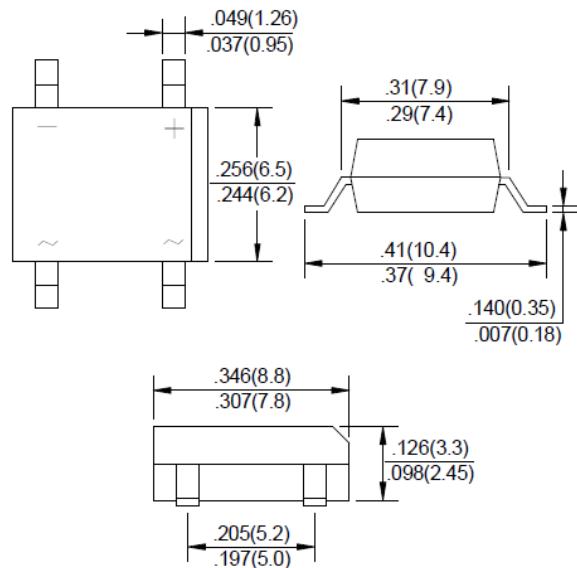
## SINGLE-PHASE GLASS PASSIVATED SILICON SURFACE MOUNT BRIDGE RECTIFIER

**Reverse Voltage - 50 to 1000 V**

**Forward Current - 1 A**

### Features

- High surge overload rating of 50 A peak
- Ideal for printed circuit board
- Low forward voltage drop
- Glass passivated chip junction



Dimensions in inches and millimeter

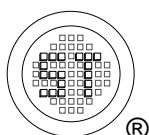
### Maximum Ratings and Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Symbols	DF005S	DF01S	DF02S	DF04S	DF06S	DF08S	DF10S	Units
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at T <sub>A</sub> = 40 °C <sup>2)</sup>	I <sub>(AV)</sub>	1							A
Peak Forward Surge Current 8.3 ms Single Half-sine-wave Superimposed on Rated Load (JEDEC Method)	I <sub>FSM</sub>	50							A
Maximum Forward Voltage at 1 A DC	V <sub>F</sub>	1.1							V
Maximum Reverse Current T <sub>A</sub> = 25 °C at Rated DC Blocking Voltage T <sub>A</sub> = 125 °C	I <sub>R</sub>	5 500							µA
Typical Junction Capacitance <sup>1)</sup>	C <sub>J</sub>	25							pF
Typical Thermal Resistance <sup>2)</sup>	R <sub>θJA</sub>	40							°C/W
Typical Thermal Resistance <sup>2)</sup>	R <sub>θJL</sub>	15							°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	- 55 to + 150							°C

<sup>1)</sup> Measured at 1 MHz and applied reverse voltage of 4 V DC.

<sup>2)</sup> Units mounted P.C.B. with 0.5 x 0.5" (13 x 13 mm) copper pads.



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